

DS40MB200

Dual 4 Gb/s 1:2 Mux/Buffer with Input Equalization and Output Pre-Emphasis

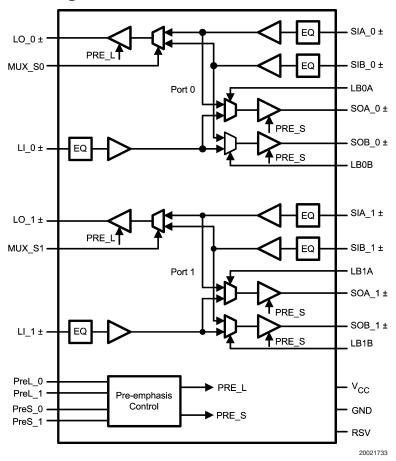
General Description

The DS40MB200 is a dual signal conditioning 2:1 multiplexer and 1:2 fan-out buffer designed for use in backplane redundancy applications. Signal conditioning features include input equalization and programmable output preemphasis that enable data communication in FR4 backplanes up to 4 Gb/s. Each input stage has a fixed equalizer to reduce ISI distortion from board traces. All output drivers have 4 selectable steps of pre-emphasis to compensate for transmission losses from long FR4 backplanes and reduce deterministic jitter. The pre-emphasis levels can be independently controlled for the line-side and switch-side drivers. The internal loopback paths from switch-side input to switch-side output enable at-speed system testing. All receiver inputs and driver outputs are internally terminated with 100Ω differential terminating resistors

Features

- Dual 2:1 multiplexer and 1:2 buffer
- 1- 4 Gbps fully differential data paths
- Fixed input equalization
- Programmable output pre-emphasis
- Independent switch and line side pre-emphasis controls
- Programmable switch-side loopback mode
- On-chip terminations
- +3.3V supply
- Low power, 1W max
- ESD rating HBM 6 kV
- Lead-less LLP-48 package (7mmx7mmx0.8mm, 0.5mm pitch)
- 0°C to +85°C operating temperature range

Functional Block Diagram



Simplified Block Diagram DS40MB200 VBB SIA_0+ M U X SIB_0+ SIB_0-MUX_S0 PORT 0 LB0A LB0B CML SOB_0+ <u>VBB</u> PreL_1 Pre-emphasis Control PRE_S PreS_0 PreS VBB SIA_1+ SIA_1-_ M U X CML SIB_1+ SIB_1-PRE_L <u>VBB</u> MUX_S1 PORT 1 LB1A LB1B SOB_1+ <u>VBB</u> SOB_1-GND pins & DAP ${\rm V_{CC}}$ pins 20021731

Connection Diagram MUX_S0 SOA_0+ SIB_0-LB0A LB0B ر دد 48 42 39 36 PreL1 PreS0 v_{cc} 35 DAP = GND v_{cc} 34 LO_0-SOB_0-33 SOB_0+ LO_0+ 32 GND GND **LLP-48** 31 LI_0+ LI_1-**Top View Shown** 30 LI_1+ LI_0-29 V_{CC} V_{CC} 28 LO_1+ SOB_1+ 10 27 SOB_1-LO_1-26 RSV GND 25 12 PreL0 PreS1 MUX_S1 SIB_1+ LB1A LB1B ر دد GND

Order number DS40MB200SQ See NS Package Number SQA48D 20021732

Pin Descriptions

Pin Name	Pin Number	I/O	Description
LINE SIDE H	IIGH SPEED D	IFFERE	NTIAL IO's
LI_0+ LI_0-	6 7	I	Inverting and non-inverting differential inputs of port_0 at the line side. LI_0+ and LI_0- have an internal 50Ω connected to an internal reference voltage.
LO_0+ LO_0-	33 34	0	Inverting and non-inverting differential outputs of port_0 at the line side. LO_0+ and LO_0- have an internal 50Ω connected to V_{CC} .
LI_1+ LI_1-	30	I	Inverting and non-inverting differential inputs of port_1 at the line side. LI_1+ and LI_1- have an internal 50Ω connected to an internal reference voltage.
LO_1+	9	0	Inverting and non-inverting differential outputs of port_1 at the line side. LO_1+ and LO_1-
LO_1-	10		have an internal 50Ω connected to V_{CC} .
	T	1	ERENTIAL IO's
SOA_0+ SOA_0-	46 45	0	Inverting and non-inverting differential outputs of mux_0 at the switch_A side. SOA_0+ and SOA_0- have an internal 50Ω connected to V_{CC} .
SOB_0+ SOB_0-	4 3	0	Inverting and non-inverting differential outputs of mux_0 at the switch_B side. SOB_0+ and SOB_0- have an internal 50Ω connected to V_{CC} .
SIA_0+ SIA_0-	40 39	I	Inverting and non-inverting differential inputs to the mux_0 at the switch_A side. SIA_0+ and SIA_0- have an internal 50Ω connected to an internal reference voltage.
SIB_0+ SIB_0-	43 42	I	Inverting and non-inverting differential inputs to the mux_0 at the switch_B side. SIB_0+ and SIB_0- have an internal 50Ω connected to an internal reference voltage.
SOA_1+	22	0	Inverting and non-inverting differential outputs of mux_1 at the switch_A side. SOA_1+ and
SOA_1-	21		SOA_1- have an internal 50Ω connected to V_{CC} .
SOB_1+ SOB_1-	28 27	0	Inverting and non-inverting differential outputs of mux_1 at the switch_B side. SOB_1+ and SOB_1- have an internal 50Ω connected to V_{CC} .
SIA_1+ SIA_1-	16 15	I	Inverting and non-inverting differential inputs to the mux_1 at the switch_A side. SIA_1+ and SIA_1- have an internal 50Ω connected to an internal reference voltage.
SIB_1+ SIB_1-	19 18	I	Inverting and non-inverting differential inputs to the mux_1 at the switch_B side. SIB_1+ and SIB_1- have an internal 50Ω connected to an internal reference voltage.
	3.3V LVCMOS)	and oib_1 mave an internal obsection to an internal relevance voltage.
MUX_S0	37	I	A logic low at MUX_S0 selects mux_0 to switch B. MUX_S0 is internally pulled high. Default state for mux_0 is switch A.
MUX_S1	13		A logic low at MUX_S1 selects mux_1 to switch B. MUX_S0 is internally pulled high. Default state for mux_1 is switch A.
PREL_0 PREL_1	12 1	I	PREL_0 and PREL_1 select the output pre-emphasis of the line side drivers (LO_0± and LO_1±). PREL_0 and PREL_1 are internally pulled high. See <i>Table 3</i> for line side pre-emphasis levels.
PRES_0 PRES_1	36 25	I	PRES_0 and PRES_1 select the output pre-emphasis of the switch side drivers (SOA_0±, SOB_0±, SOA_1± and SOB_1±). PRES_0 and PRES_1 are internally pulled high. See <i>Table 4</i> for switch side pre-emphasis levels.
LB0A	47	1	A logic low at LB0A enables the internal loopback path from SIA_0± to SOA_0±. LB0A is internally pulled high.
LB0B	48	I	A logic low at LB0B enables the internal loopback path from SIB_0± to SOB_0±. LB0B is internally pulled high.
LB1A	23	I	A logic low at LB1A enables the internal loopback path from SIA_1± to SOA_1±. LB1A is internally pulled high.
LB1B	24	I	A logic low at LB1B enables the internal loopback path from SIB_1± to SOB_1±. LB1B is internally pulled high.
RSV	26	I	Reserve pin to support factory testing. This pin can be left open, or tied to GND, or tied to GND through an external pull-down resistor.

Pin Descriptions (Continued)

Pin Name	Pin Number	I/O	Description		
POWER					
V _{CC}	2, 8, 14, 20, 29, 35, 38, 44	Р	$V_{\rm CC}$ = 3.3V ± 5%. Each $V_{\rm CC}$ pin should be connected to the $V_{\rm CC}$ plane through a low inductance path, typically with a via located as close as possible to the landing pad of the $V_{\rm CC}$ pin. It is recommended to have a 0.01 μF or 0.1 μF, X7R, size-0402 bypass capacitor from each $V_{\rm CC}$ pin to ground plane.		
GND	5, 11, 17, 32, 41	Р	Ground reference. Each ground pin should be connected to the ground plane through a low inductance path, typically with a via located as close as possible to the landing pad of the GND pin.		
GND	DAP	Р	Die Attach Pad (DAP) is the metal contact at the bottom side, located at the center of the LLP-48 package. It should be connected to the GND plane with at least 4 via to lower the ground impedance and improve the thermal performance of the package.		

Note: I = Input, O = Output, P = Power

Functional Description

The DS40MB200 is a signal conditioning 2:1 multiplexer and a 1:2 buffer designed to support port redundancy up to 4 Gb/s. Each input stage has a fixed equalizer that provides equalization to compensate about 5 dB of transmission loss from a short backplane trace (about 10 inches backplane). The output driver has pre-emphasis (driver-side equalization) to compensate the transmission loss of the backplane that it is driving. The driver conditions the output signal such that the lower frequency and higher frequency pulses reach approximately the same amplitude at the end of the backplane, and minimize the deterministic jitter caused by the

amplitude disparity. The DS40MB200 provides 4 steps of user-selectable pre-emphasis ranging from 0, -3, -6 and -9 dB to handle different lengths of backplane. Figure 1 shows a driver pre-emphasis waveform. The pre-emphasis duration is 200ps nominal, corresponds to 0.75 bit-width at 4 Gb/s. The pre-emphasis levels of switch-side and line-side can be individually programmed.

The high speed inputs are self-biased to about 1.5V and are designed for AC coupling. The inputs are compatible to most AC coupling differential signals such as LVDS, LVPECL and CML.

TABLE 1. LOGIC TABLE FOR MULTIPLEX CONTROLS

MUX_S0	Mux Function
0	MUX_0 select switch_B input, SIB_0±.
1 (default)	MUX_0 select switch_A input, SIA_0±.
MUX_S1	Mux Function
0	MUX_1 select switch_B input, SIB_1±.

TABLE 2. LOGIC TABLE FOR LOOPBACK Controls

LB0A	Loopback Function
0	Enable loopback from SIA_0± to SOA_0±.
1 (default)	Normal mode. Loopback disabled.
LB0B	Loopback Function
0	Enable loopback from SIB_0± to SOB_0±.
1 (default)	Normal mode. Loopback disabled.
LB1A	Loopback Function
0	Enable loopback from SIA_1± to SOA_1±.
1 (default)	Normal mode. Loopback disabled.
LB1B	Loopback Function
0	Enable loopback from SIB_1± to SOB_1±.
1 (default)	Normal mode. Loopback disabled.

Functional Description (Continued)

TABLE 3. LINE-SIDE PRE-EMPHASIS CONTROLS

PreL_[1:0]	Pre-Emphasis Level in mV _{PP} (VODB)	De-Emphasis Level in mV _{PP} (VODPE)	Pre-Emphasis in dB (VODPE/VODB)	Typical FR4 board trace
0 0	1200	1200	0	10 inches
0 1	1200	850	-3	20 inches
1 0	1200	600	-6	30 inches
1 1 (default)	1200	426	-9	40 inches

TABLE 4. SWITCH-SIDE PRE-EMPHASIS CONTROLS

PreS_[1:0]	Pre-Emphasis Level in mV _{PP} (VODB)	De-Emphasis Level in mV _{PP} (VODPE)	Pre-Emphasis in dB (VODPE/VODB)	Typical FR4 board trace
0 0	1200	1200	0	10 inches
0 1	1200	850	-3	20 inches
1 0	1200	600	-6	30 inches
1 1 (default)	1200	426	-9	40 inches

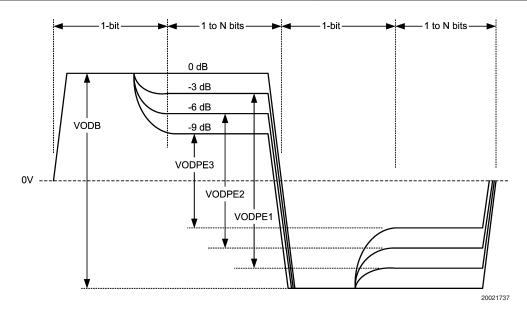


FIGURE 1. Driver Pre-Emphasis Differential Waveform (showing all 4 pre-emphasis steps)

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Supply Voltage (V _{CC})	-0.3V to 4V
CMOS/TTL Input Voltage	-0.3V to
	$(V_{CC} + 0.3V)$
CML Input/Output Voltage	-0.3V to

(V_{CC} +0.3V) +125°C

Junction Temperature $+125^{\circ}$ C Storage Temperature -65° C to $+150^{\circ}$ C

Lead Temperature

Soldering, 4 sec $+260^{\circ}$ C Thermal Resistance, θ_{JA} 33.7°C/W

Thermal Resistance, $\theta_{\text{JC-top}}$	20.7°C/W
Thermal Resistance, $\theta_{\text{JC-bottom}}$	5.8°C/W
Thermal Resistance, Φ_{JB}	18.2°C/W
ESD Rating HBM, 1.5 k Ω , 100 pF	6 kV
ESD Rating Machine Model	250V

Recommended Operating Ratings

	Min	Тур	Max	Units
Supply Voltage (V _{CC} -GND)	3.135	3.3	3.465	V
Supply Noise Amplitude			20	mV_PP
10 Hz to 2 GHz				
Ambient Temperature	0		85	°C
Case Temperature			100	°C

Electrical Characteristics

Over recommended operating supply and temperature ranges unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ (Note 2)	Max	Units
LVCMOS	DC SPECIFICATIONS		•		•	•
V _{IH}	High Level Input Voltage		2.0		V _{CC} +0.3	V
V _{IL}	Low Level Input Voltage		-0.3		0.8	V
I _{IH}	High Level Input Current	$V_{IN} = V_{CC}$	-10		10	μΑ
I _{IL}	Low Level Input Current	V _{IN} = GND	75	94	124	μΑ
R _{PU}	Pull-High Resistance			35		kΩ
RECEIVER	RSPECIFICATIONS		•	•	•	
V_{ID}	Differential Input Voltage Range	AC Coupled Differential Signal Below 1.25 Gb/s At 1.25 Gbps-3.125 Gbps Above 3.125 Gbps This parameter is not production tested.	100 100 100		1750 1560 1200	mV _{P-P} mV _{P-P} mV _{P-P}
V _{ICM}	Common Mode Voltage at Receiver Inputs	Measured at receiver inputs reference to ground.		1.3		V
R _{ITD}	Input Differential Termination	On-chip differential termination between IN+ or IN	84	100	116	Ω
R _{ITSE}	Input Termination (single-end)	On-chip termination IN+ or IN- to GND for frequency > 100 MHz.		50		Ω
DRIVER S	PECIFICATIONS		•	•	•	•
VODB	Output Differential Voltage Swing without Pre-Emphasis	R _L = 100Ω ±1% PRES_1=PRES_0=0 PREL_1=PREL_0=0 Driver pre-emphasis disabled. Running K28.7 pattern at 4 Gbps. See Figure 5 for test circuit.	1000	1200	1400	mV _{P-P}

Electrical Characteristics (Continued)
Over recommended operating supply and temperature ranges unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ (Note 2)	Max	Units
DRIVER S	PECIFICATIONS					
V_{PE}	Output Pre-Emphasis	$R_{L} = 100\Omega \pm 1\%$				
	Voltage Ratio	Running K28.7 pattern at 4 Gbps				
	20*log(VODPE/VODB)			0		dB
		PREx_[1:0]=01		-3		dB
		PREx_[1:0]=10		-6		dB
		PREx_[1:0]=10		_9		dB
				_9		uБ
		x=S for switch side pre-emphasis control				
		x=L for line side pre-emphasis control				
		See Figure 1 on waveform.				
		See Figure 5 for test circuit.				
t _{PE}	Pre-Emphasis Width	Tested at -9 dB pre-emphasis level,				
	(Note 8)	PREx[1:0]=11				
		x=S for switch side pre-emphasis control	125	200	250	ps
		x=L for line side pre-emphasis control				
		See Figure 4 on measurement condition.				
R _{OTSE}	Output Termination	On-chip termination from OUT+ or OUT- to				
OTSE	Output Terrimation		42	50	58	Ω
	Outrat Differential	V _{CC}				
R_{OTD}	Output Differential	On-chip differential termination between OUT+		100		Ω
	Termination	and OUT-				
ΔR_{OTSE}	Mis-Match in Output	Mis-match in output terminations at OUT+ and				
	Termination	OUT-			5	%
	Resistors					
V _{OCM}	Output Common					
00	Mode Voltage			2.7		V
POWER D	ISSIPATION					
P _D	Power Dissipation	V _{DD} = 3.465V				
D	'	All outputs terminated by $100\Omega \pm 1\%$.				
		PREL_[1:0]=0, PRES_[1:0]=0			1	W
		Running PRBS 2 ⁷ -1 pattern at 4 Gbps				
AC CHAR	ACTERISTICS	ridining i ribo 2 i pattori at 4 dopo				
t _R	Differential Low to	Measured with a clock-like pattern at				
⁴ R	High Transition Time	100 MHz, between 20% and 80% of the				
	nigh fransition fille			80		ps
		differential output voltage. Pre-emphasis				
t _F	Differential High to	disabled.				
1	Low Transition Time	Transition time is measured with fixture as		80		200
		shown in Figure 5, adjusted to reflect the		00		ps
		transition time at the output pins.				
t _{PLH}	Differential Low to	Measured at 50% differential voltage from				
	High Propagation	input to output.		0.5	2	ns
	Delay					
t _{PHL}	Differential High to					
FUL	Low Propagation			0.5	2	ns
	Delay			0.5	_	110
+	Pulse Skew (Note 8)	lt _t			20	ne
t _{SKP}		t _{PHL} -t _{PLH}			20	ps
t _{sko}	Output Skew	Difference in propagation delay among data			200	ps
	(Notes 7, 8)	paths in the same device.			_,,	
t _{SKPP}	Part-to-Part Skew	Difference in propagation delay between the				
SKEE	1	anno autout fram daviana anaratina undar		1	500	no
SKEF	(Note 8)	same output from devices operating under			500	ps

Electrical Characteristics (Continued)

Over recommended operating supply and temperature ranges unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ (Note 2)	Max	Units
AC CHAR	AC CHARACTERISTICS					
t _{SM}	Mux Switch Time	Measured from V_{IH} or V_{IL} of the mux-control or loopback control to 50% of the valid differential output.		1.8	6	ns
RJ	Device Random Jitter (Note 5) (Note 8)	See Figure 5 for test circuit. Alternating-1-0 pattern. Pre-emphasis disabled. At 1.25 Gbps At 4 Gbps			2 2	psrms psrms
DJ	Device Deterministic Jitter (Note 6) (Note 8)	See Figure 5 for test circuit. Pre-emphasis disabled. At 4 Gbps, PRBS7 pattern			30	pspp
DR _{MAX}	Maximum Data Rate (Note 8)	Tested with alternating-1-0 pattern	4			Gbps

Note 1: "Absolute Maximum Ratings" are the ratings beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits.

Note 2: Typical parameters measured at $V_{CC} = 3.3V$, $T_A = 25$ °C. They are for reference purposes and are not production-tested.

Note 3: IN+ and IN- are generic names refer to one of the many pairs of complimentary inputs of the DS40MB200. OUT+ and OUT- are generic names refer to one of the many pairs of the complimentary outputs of the DS40MB200. Differential input voltage V_{ID} is defined as IIN+-IN-I. Differential output voltage V_{OD} is defined as IOUT+-OUT-I.

Note 4: K28.7 pattern is a 10-bit repeating pattern of K28.7 code group {001111 1000}

K28.5 pattern is a 20-bit repeating pattern of +K28.5 and -K28.5 code groups {110000 0101 001111 1010}

Note 5: Device output random jitter is a measurement of the random jitter contribution from the device. It is derived by the equation $sqrt(RJ_{OUT}^2 - RJ_{IN}^2)$, where RJ_{OUT} is the total random jitter measured at the output of the device in psrms, RJ_{IN} is the random jitter of the pattern generator driving the device.

Note 6: Device output deterministic jitter is a measurement of the deterministic jitter contribution from the device. It is derived by the equation (DJ_{OUT}–DJ_{IN}), where DJ_{OUT} is the total peak-to-peak deterministic jitter measured at the output of the device in pspp, DJ_{IN} is the peak-to-peak deterministic jitter of the pattern generator driving the device.

Note 7: t_{SKO} is the magnitude difference in the propagation delays among data paths between switch A and switch B of the same port and similar data paths between port 0 and port 1. An example is the output skew among data paths from SIA_0± to LO_0±, SIB_0± to LO_0±, SIA_1± to LO_1± and SIB_1± to LO_1±. Another example is the output skew among data paths from LI_0± to SOA_0±, LI_0± to SOB_0±, LI_1± to SOA_1± and LI_1± to SOB_1±. t_{SKO} also refers to the delay skew of the loopback paths of the same port and between similar data paths between port 0 and port 1. An example is the output skew among data paths SIA_0± to SOA_0±, SIB_0± to SOB_0±, SIA_1± to SOA_1± and SIB_1± to SOB_1±.

Note 8: Guaranteed by desigh and characterization using statistical analysis.

Timing Diagrams

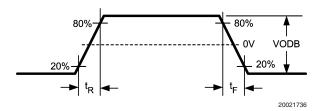


FIGURE 2. Driver Output Transition Time

Timing Diagrams (Continued)

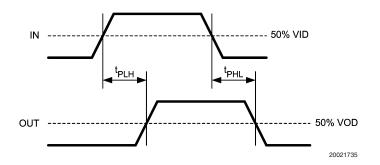


FIGURE 3. Propagation Delay from input to output

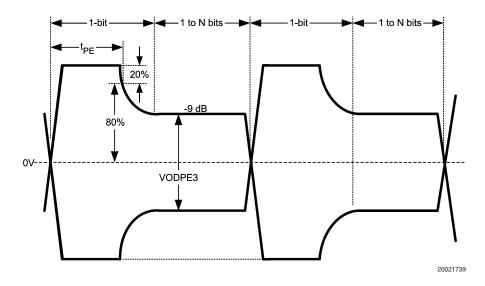


FIGURE 4. Test condition for output pre-emphasis duration

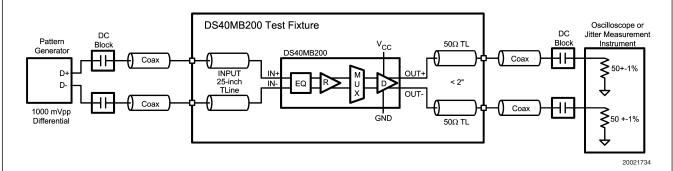


FIGURE 5. AC Test Circuit

The DS40MB200 input equalizer provides equalization to compensate about 5 dB of transmission loss from a short backplane transmission line. For characterization purposes, a 25-inch FR4 coupled micro-strip board trace is used in place of the short backplane link. The 25-inch microstrip board trace has approximately 5 dB of attenuation between

375 MHz and 1.875 GHz, representing closely the transmission loss of the short backplane transmission line. The 25-inch microstrip is connected between the pattern generator and the differential inputs of the DS40MB200 for AC measurements.

Timing Diagrams (Continued)

	Finished Trace	Separation between		Dielectric Constant	
Trace Length	Width W	Traces	Dielectric Height H	€R	Loss Tangent
25 inches	8.5 mil	11.5 mil	6 mil	3.8	0.022

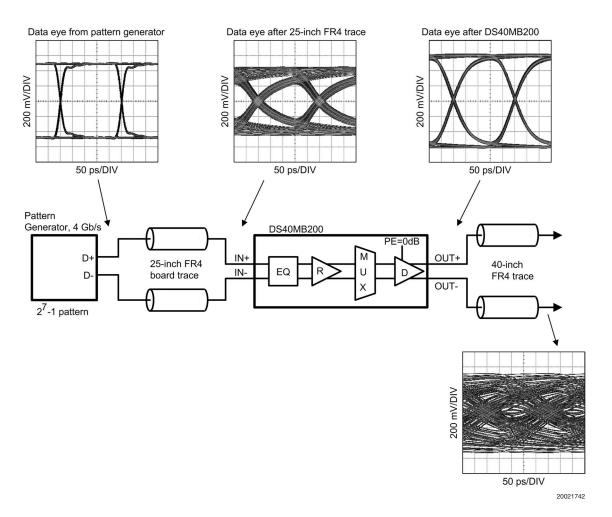


FIGURE 6. Data input and output eye patterns with driver set to 0 dB pre-emphasis

Timing Diagrams (Continued)

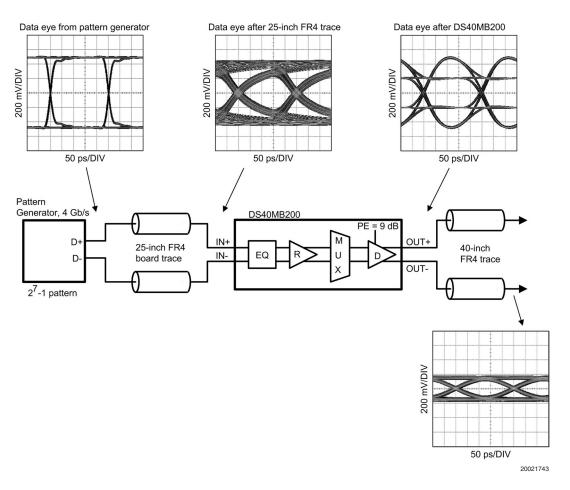


FIGURE 7. Data input and output eye patterns with driver set to 9dB pre-emphasis

Application Information

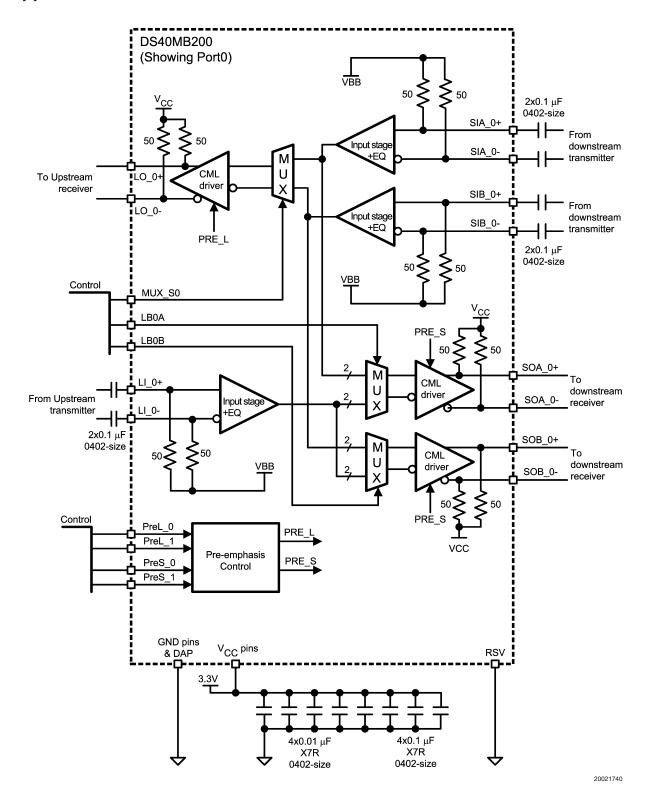


FIGURE 8. Application diagram (showing data paths of port 0)

Physical Dimensions inches (millimeters) unless otherwise noted 000000000000 (48X 0 25 DIMENSIONS ARE IN MILLIMETERS MENSIONS IN () FOR REFERENCE ONL (□4 .1) | 000000| 000000 - C RECOMMENDED LAND PATTERN 4 X 5 . 5 0.8 MAX - 44X 0.5 PIN 1 INDEX AREA (0.2) \bigcup □4.1±0.1 7+0 1 \cup 48X 0.45±0.1 В _ A SQA48D (Rev A)

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